

**Model Question Paper**  
**Third Semester B.E Degree(CBCS) Examination**  
**Analog Electronic circuits**

Time : 3hrs

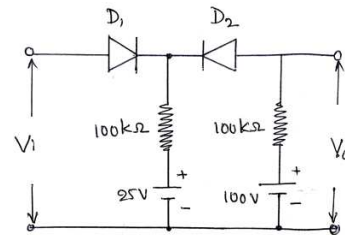
Max Marks:100

Note: Answer FIVE full questions, choosing one full question from each module

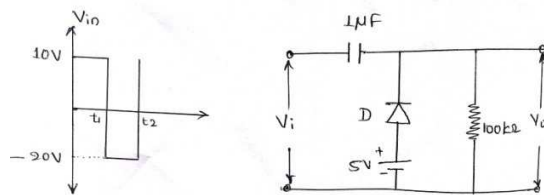
**Module 1**

1 a Draw a double ended clipper circuit and explain its working principle with transfer characteristics. 7 Marks

b For the sketch shown fig. below,  $V_i$  varies from 0 to 150 V, sketch the output voltage  $V_o$  to the same time scale as the input voltage. Assume ideal diode 7 Marks



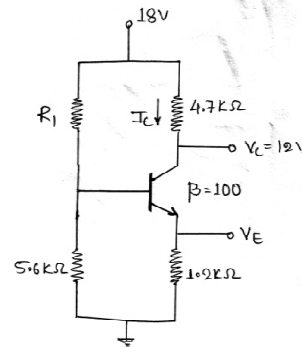
c Write the procedure for analyzing the clamping circuit, determine output voltage for the network shown in fig. (1.b) Assume  $f=1000\text{Hz}$  and ideal diode. 6 Marks



**or**

2 a Consider a fixed bias circuit of a transistor. Obtain expressions for stability factor  $S_{I_{C0}}$ ,  $S_{V_{BE}}$  and  $S_{\beta}$ . Draw the circuit diagram 9 Marks

b For the circuit shown in fig. find  $I_C$ ,  $V_B$ ,  $V_E$ ,  $R_1$  and  $S_{I_{C0}}$  7 Marks



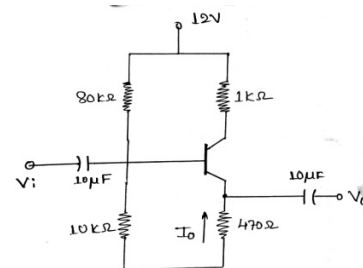
c Define operating point. Explain its significance 4 Marks

**Module 2**

3 a Obtain r-parameter model for CE configuration. 5 Marks

b Draw the circuit of common base amplifier. Derive the expression for current gain, voltage gain, input and output impedance using the model 7 Marks

c For the emitter follower circuit shown in fig. obtain the values of  $r_e$ ,  $Z_i$ ,  $Z_o$ , voltage gain ( $A_V$ ) and current gain ( $A_I$ ). assume  $\beta=100$  and  $r_o=50k\Omega$  8 Marks



**Model Question Paper**  
**Third Semester B.E Degree(CBCS) Examination**  
**Analog Electronic circuits**

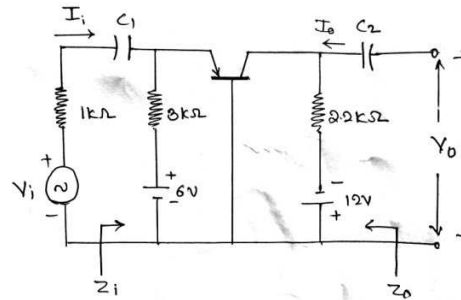
Time : 3hrs

Max Marks:100

Note: Answer FIVE full questions, choosing one full question from each module

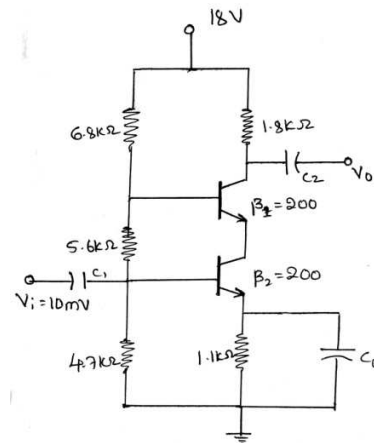
**or**

- 4 a Define h parameters and hence derive h-parameter model of CC-BJT 6 Marks  
 b State and prove miller's theorem 6 Marks  
 c For common base amplifier shown in fig. determine  $Z_i$ ,  $A_I$ ,  $A_V$ , and  $Z_O$  using complete hybrid equivalent model. (Given  $h_{ie}=1.6k\Omega$ ,  $h_{fe}=100$ ,  $h_{re}=2 \times 10^{-4}$ ,  $h_{oe}=20\mu S$ .) 8 Marks



**Module 3**

- 5 a Draw the circuit of Darlington emitter follower. Derive the expression for current gain, voltage gain, input and output impedance using the model. 10Marks  
 b For the cascode circuit shown below calculate 10 Marks  
 a) The dc bias voltages  $V_{B1}, V_{B2}, V_{C2}$   
 b) The no load voltage gain and the output voltages  $V_{O2}=V_O$   
 c) The voltage gain with load of  $10k\Omega$  connected to the second stage and the output voltage  $V_O$   
 d) Input and output impedances



**or**

- 6 a For the voltage series feedback amplifier topology, obtain expression for  $A_V$  and  $R_{if}$ . Also explain the principle of voltage amplifier used in feedback amplifiers. 10 Marks  
 b List and explain the advantages of employing negative feedback in amplifiers 6 Marks  
 c Explain the difference between cascade and cascode connections and its applications 4 Marks

**Module 4**

- 7 a With a neat diagram explain transformer coupled power amplifier and derive the expression for AC power delivered to the load, show that the maximum efficiency is 50%. 10 Marks  
 b State and explain Barkhausen criterion for sustained oscillations. 5 Marks  
 c A crystal has following parameters: 5 Marks  
 $L=0.334H$ ,  $C= 0.065pF$ ,  $CM=1pF$ ,  $R=5.5k\Omega$   
 Calculate series resonant frequency.  
 Calculate parallel resonant frequency.

**Model Question Paper**  
**Third Semester B.E Degree(CBCS) Examination**  
**Analog Electronic circuits**

Time : 3hrs

Max Marks:100

Note: Answer FIVE full questions, choosing one full question from each module

Find Q of the crystal.

**or**

- 8 a Explain the working of complementary symmetry class B amplifier **6 Marks**  
 b Derive an expression for frequency of oscillations in wien bridge oscillator **8 Marks**  
 c Find the values of  $R_C$ ,  $R$ ,  $R'$  and  $C$  for an RC  $-$ phase shift oscillator for a frequency of oscillation of 1000 Hz. A transistor is having  $h_{fe}=200$  and  $h_{ie}=2k\Omega$ . **6 Marks**

**Module 5**

- 9 a Draw the circuit for JFET common source amplifier using fixed biased configuration and determine its input impedance, output impedance and voltage gain using ac equivalent small signal model **10 Marks**  
 b Explain the working and construction of JFET in detail and draw its transfer characteristics and drain characteristics. **10 Marks**

**or**

- 10 a Explain the depletion and enhancement type MOSFETs, their characteristics and frequency response **10 Marks**  
 b For the circuit shown in fig. **10 Marks**  
 a) Calculate  $Z_i$  and  $Z_o$   
 b) Calculate  $A_v$   
 c) Calculate  $V_o$ , for  $V_i=1mV(rms)$   
 d) Repeat from (a) to (c) neglecting the effect of  $r_d$

(Given  $I_{DSS}=12mA$ ,  $V_P=-3.5V$ ,  $V_{GSQ}=-0.75V$ ,  $r_d=50k\Omega$ )

